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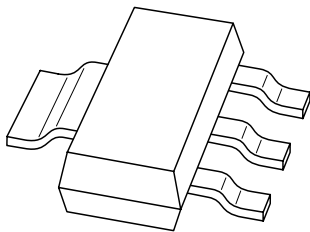
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Kind regards,

Team Nexperia

DATA SHEET



BSP60; BSP61; BSP62 PNP Darlington transistors

Product data sheet
Supersedes data of 1999 Apr 29

2001 May 31

PNP Darlington transistors

BSP60; BSP61; BSP62

FEATURES

- High current (max. 0.5 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

APPLICATIONS

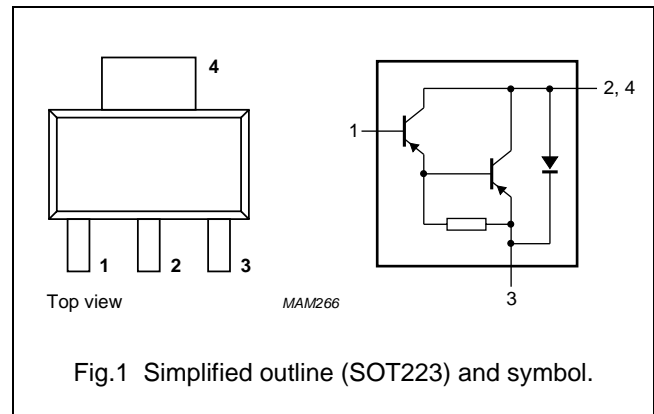
- Industrial switching applications such as:
 - Print hammer
 - Solenoid
 - Relay and lamp drivers.

DESCRIPTION

PNP Darlington transistor in a SOT223 plastic package.
NPN complements: BSP50, BSP51 and BSP52.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter			
	BSP60		–	–60	V
	BSP61		–	–80	V
V _{CES}	collector-emitter voltage	V _{BE} = 0			
	BSP60		–	–45	V
	BSP61		–	–60	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
	I _C	collector current (DC)	–	–1	A
	I _{CM}	peak collector current	–	–2	A
I _B	base current (DC)		–	–100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	1.25	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “Thermal considerations for the SOT223 in the General Part of associated Handbook”.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	98	K/W
$R_{th\ j-s}$	thermal resistance from junction to solder point		17	K/W

Note

- Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².
For other mounting conditions, see "Thermal considerations for the SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

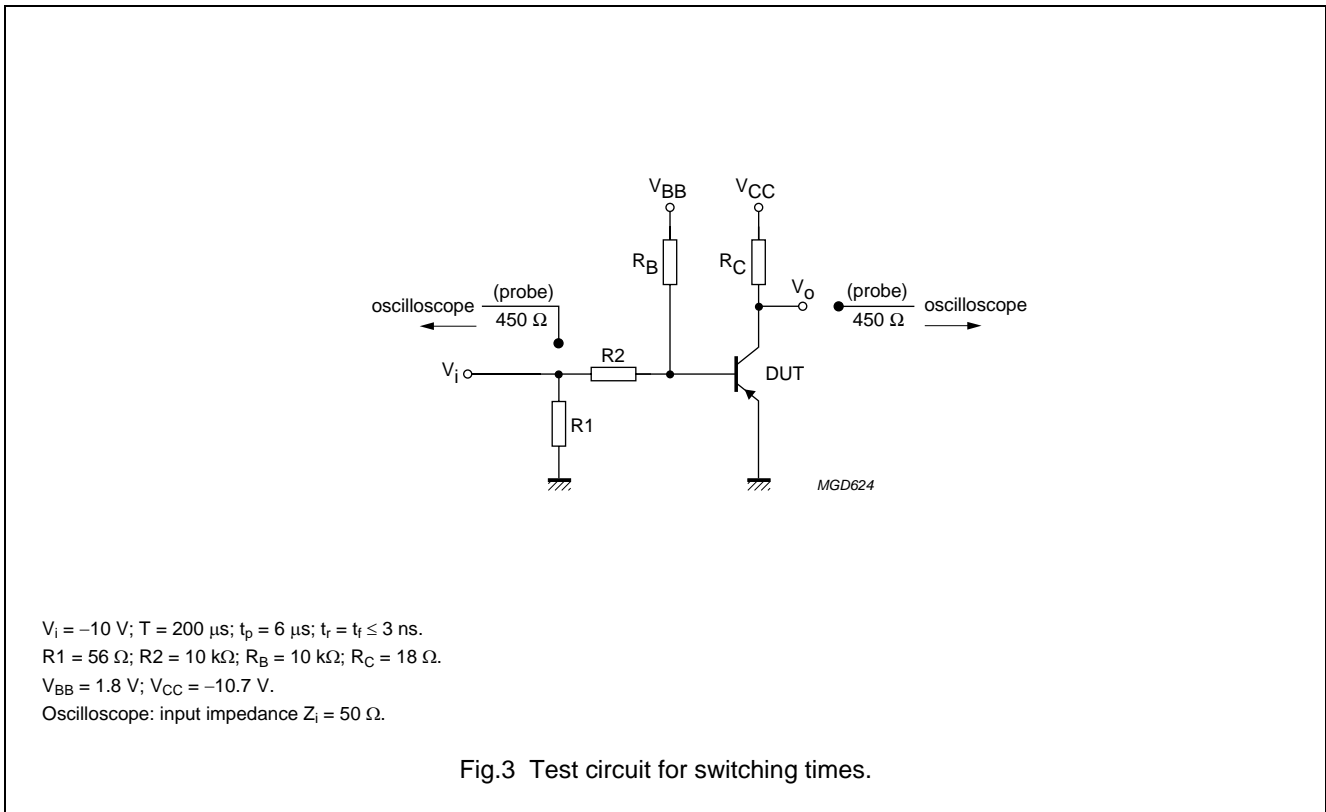
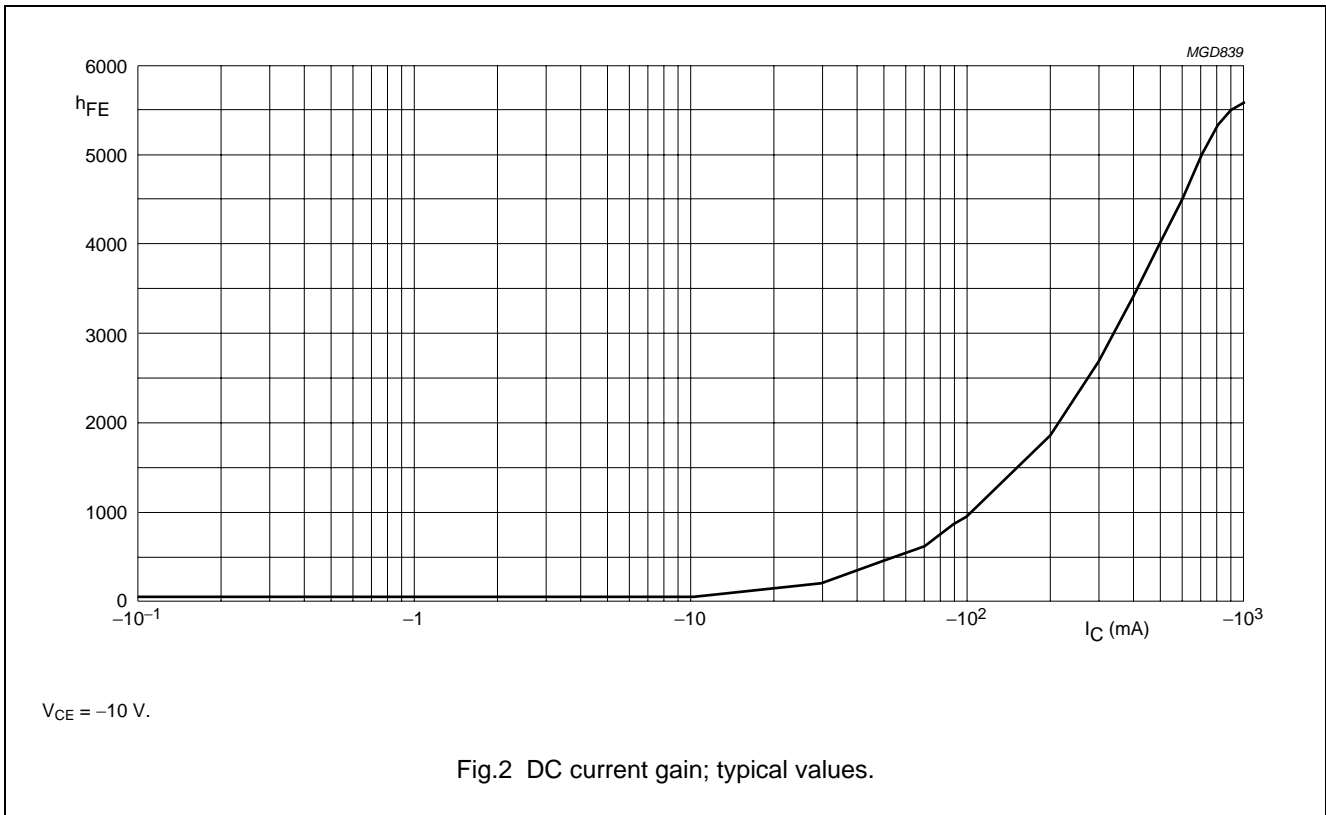
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	collector cut-off current					
	BSP60	$V_{BE} = 0; V_{CE} = -45\text{ V}$	–	–	–50	nA
	BSP61	$V_{BE} = 0; V_{CE} = -60\text{ V}$	–	–	–50	nA
	BSP62	$V_{BE} = 0; V_{CE} = -80\text{ V}$	–	–	–50	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -4\text{ V}$	–	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}$; note 1; see Fig.2				
		$I_C = -150\text{ mA}$	1000	–	–	
		$I_C = -500\text{ mA}$	2000	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -0.5\text{ mA}$	–	–	–1.3	V
		$I_C = -500\text{ mA}; I_B = -0.5\text{ mA}; T_j = 150\text{ °C}$	–	–	–1.3	V
V_{BEsat}	base-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -0.5\text{ mA}$	–	–	–1.9	V
f_T	transition frequency	$I_C = -500\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	–	200	–	MHz
Switching times (between 10% and 90% levels); see Fig.3						
t_{on}	turn-on time	$I_{Con} = -500\text{ mA}; I_{Bon} = -0.5\text{ mA}; I_{Boff} = 0.5\text{ mA}$	–	400	–	ns
t_{off}	turn-off time		–	1500	–	ns

Note

- Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

PNP Darlington transistors

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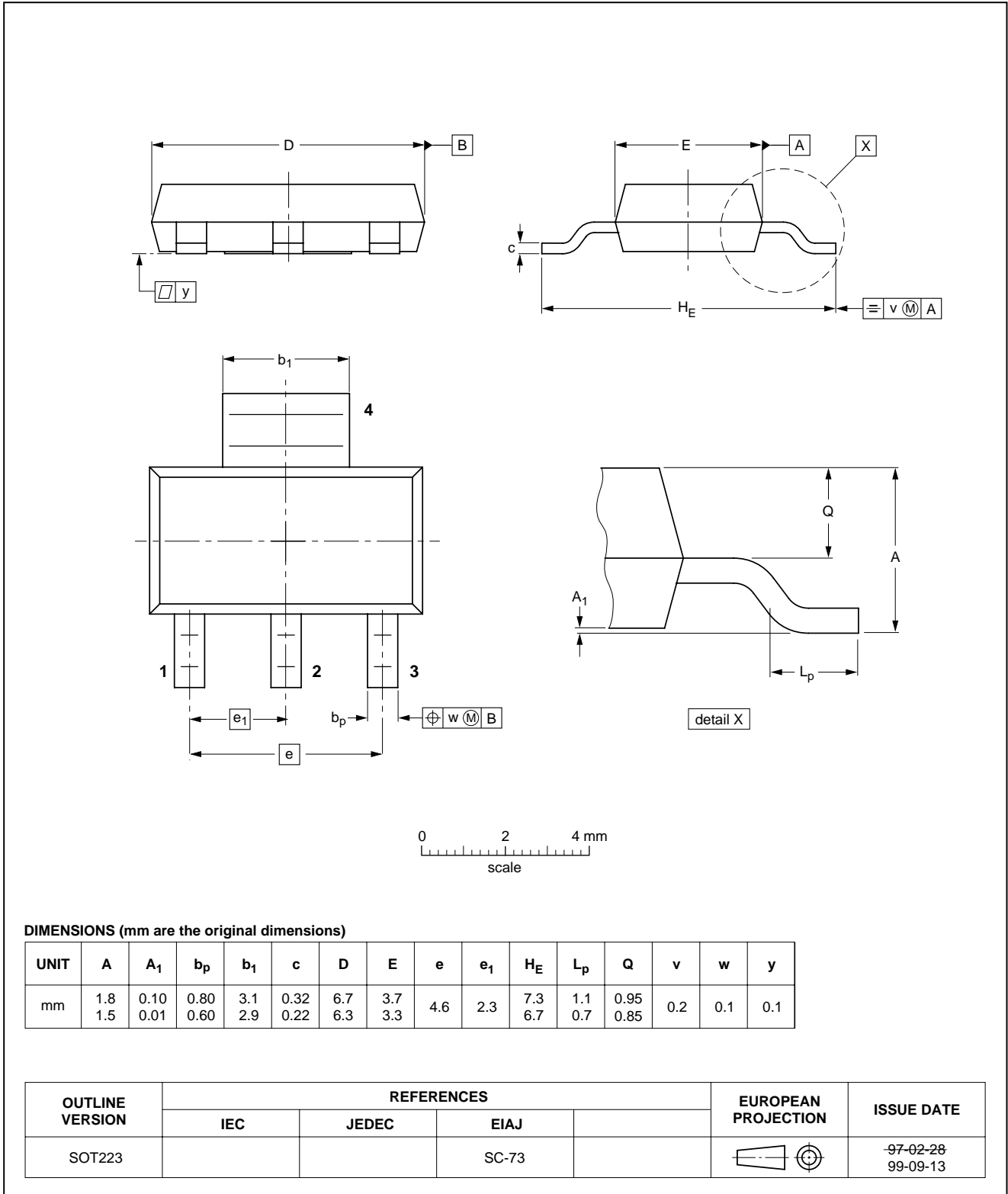
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



PNP Darlington transistors

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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